

# OptiMOS<sup>®</sup>2 – 30V Trench Technology in DPAK

IFX Products	V <sub>DS</sub> in V	R <sub>DSon(max)</sub> @ 10V in mΩ	R <sub>DSon(max)</sub> @ 4,5V in mΩ	Q <sub>g</sub> (typ) @ 5V in nC	Eng. Samples	Mass Production
IPD03N03LB	30	3,3	4,9	33	September 04	Dec 04
IPD04N03LB	30	4,1	5,8	30	August 04	Oct 04
IPD05N03LB	30	4,8	7,5	19	September 04	Dec 04
IPD06N03LB	30	6,1	9,1	16	August 04	Oct 04
IPD09N03LB	30	9,1	14,2	10	August 04	Oct 04
IPD12N03LB	30	11,6	17,7	8	August 04	Oct 04

Very low on-state resistance RDS(on)



- Minimized on-state power dissipation
- Low conduction losses

Low gate charge Qg / low gate resistance Rg



Very low switching losses

Low Qrr in intrinsic body diode



Low reverse recovery losses

High ruggedness regarding avalanche and short circuit



Safe operation in inductive circuits

Never stop thinking